



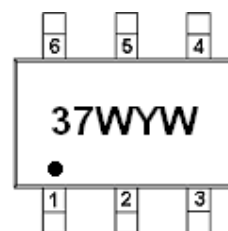
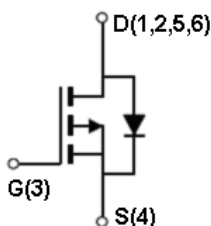
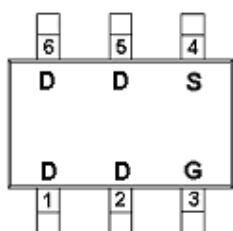
General Description

AFP3437W, P-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge. These devices are particularly suited for low voltage power management, and low in-line power loss are needed in commercial industrial surface mount applications.

Features

- -100V/-1.4A, $R_{DS(ON)}=750m\Omega@V_{GS}=-10V$
- -100V/-1.0A, $R_{DS(ON)}=800m\Omega@V_{GS}=-4.5V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- TSOP-6 package design

Pin Description (TSOP-6)



Application

- Active Clamp Circuits in DC/DC Power Supplies

Pin Define

Pin	Symbol	Description
1	D	Drain
2	D	Drain
3	G	Gate
4	S	Source
5	D	Drain
6	D	Drain

Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFP3437WTS6RG	37WYW	TSOP-6	Tape & Reel	3000 EA

- ※ 37W parts code
- ※ Y year code (0 ~ 9)
- ※ W week code (A ~ Z = 1 ~ 26 / a ~ z = 27 ~ 52)
- ※ AFP3437WTS6RG : 7" Tape & Reel ; Pb- Free ; Halogen -Free



Absolute Maximum Ratings

(T_A=25°C Unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	-100	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current(T _J =150°C)	I _D	T _c =25°C	-1.4
		T _c =70°C	-1.0
Pulsed Drain Current	I _{DM}	-5	A
Continuous Source Current(Diode Conduction)	I _S	-1.5	A
Power Dissipation	P _D	T _A =25°C	2.0
		T _A =70°C	1.3
Operating Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{STG}	-55/150	°C
Thermal Resistance-Junction to Ambient	R _{θJA}	120	°C/W

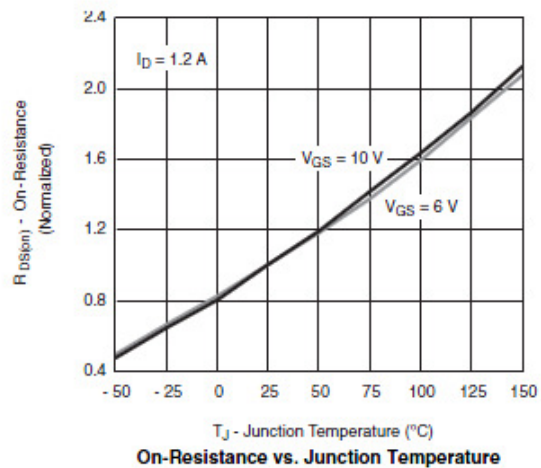
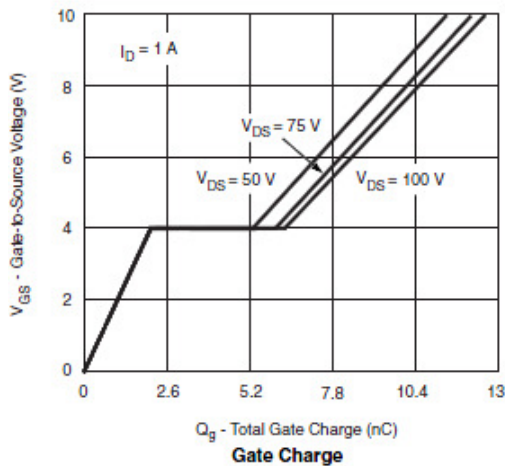
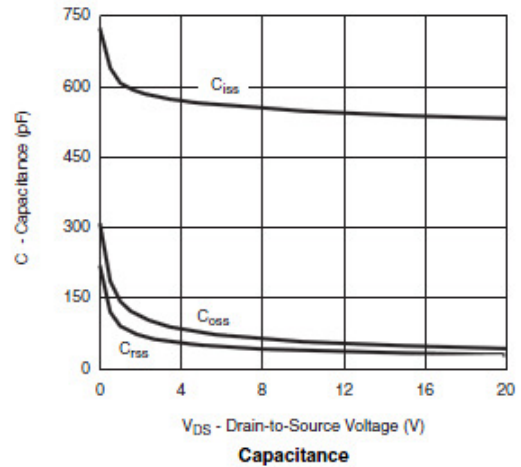
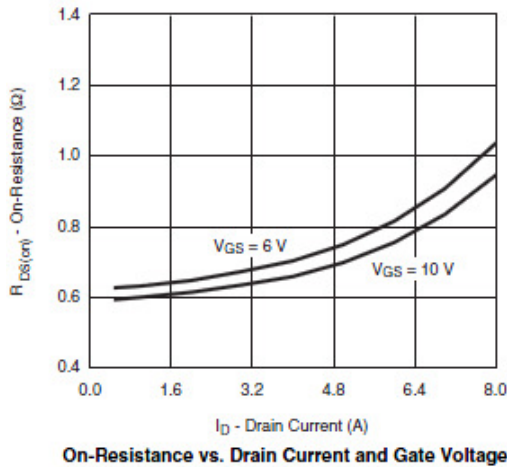
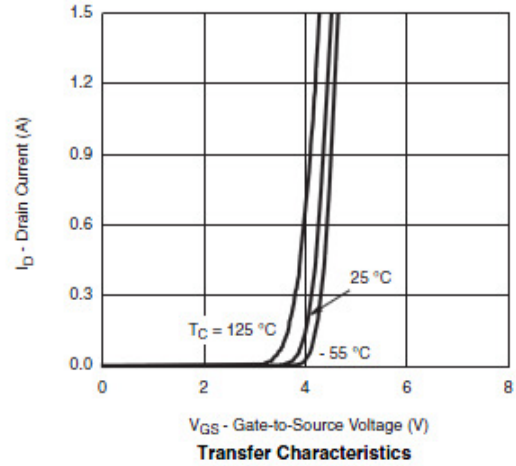
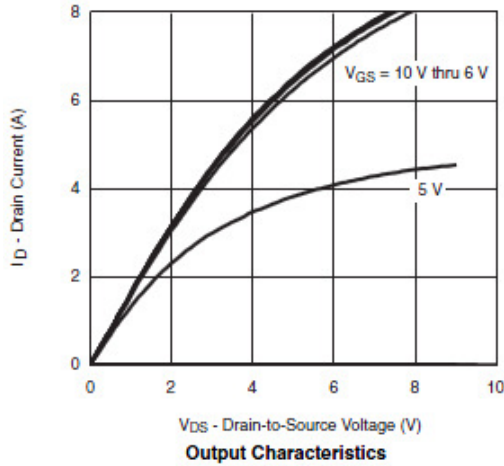
Electrical Characteristics

(T_A=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =-250uA	-100			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250uA	-1.0	-1.8	-2.5	
Gate Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-80V, V _{GS} =0V			-1	uA
		V _{DS} =-80V, V _{GS} =0V T _J =85°C			-30	
On-State Drain Current	I _{D(on)}	V _{DS} ≥ -10V, V _{GS} =-10V	-3			A
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-1.4A		650	750	mΩ
		V _{GS} =-4.5V, I _D =-1.0A		700	800	
Forward Transconductance	g _{FS}	V _{DS} =-10V, I _D =-1.4A		4.5		S
Diode Forward Voltage	V _{SD}	I _S =-1.0A, V _{GS} =0V		-0.75	-1.2	V
Dynamic						
Total Gate Charge	Q _g	V _{DS} =-75V, V _{GS} =-6V I _D ≡-1.0A		8	12	nC
Gate-Source Charge	Q _{gs}			2		
Gate-Drain Charge	Q _{gd}			4		
Input Capacitance	C _{iss}	V _{DS} =-50V, V _{GS} =0V f=1MHz		500		pF
Output Capacitance	C _{oss}			30		
Reverse Transfer Capacitance	C _{rss}			20		
Turn-On Time	t _{d(on)}	V _{DD} =-75V, R _L =75Ω I _D ≡-1.0A, V _{GEN} =-10V R _G =1.0Ω		10	20	ns
	t _r			12	25	
Turn-Off Time	t _{d(off)}			25	50	
	t _f			12	25	

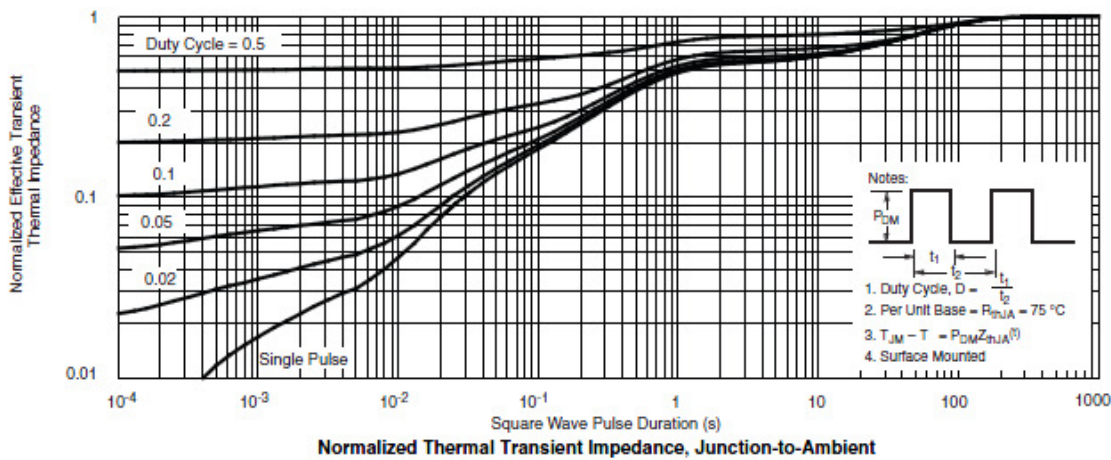
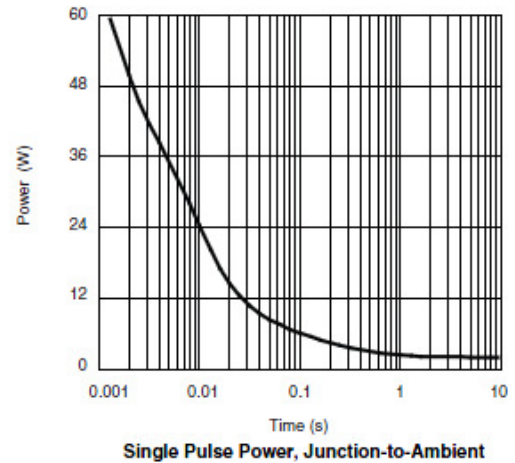
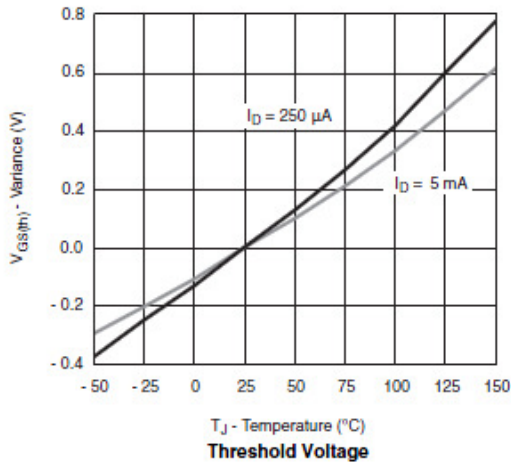
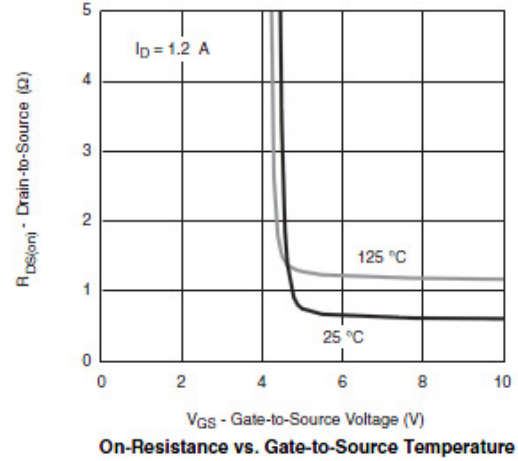
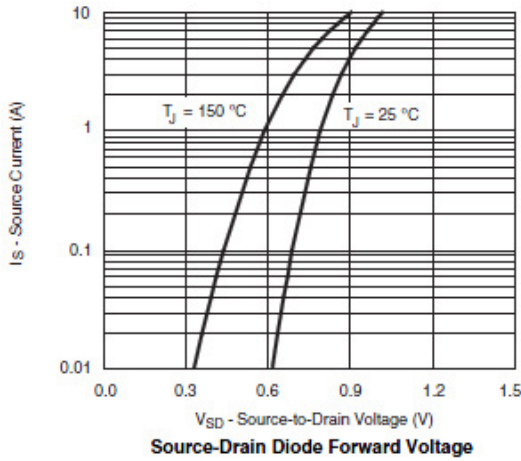


Typical Characteristics





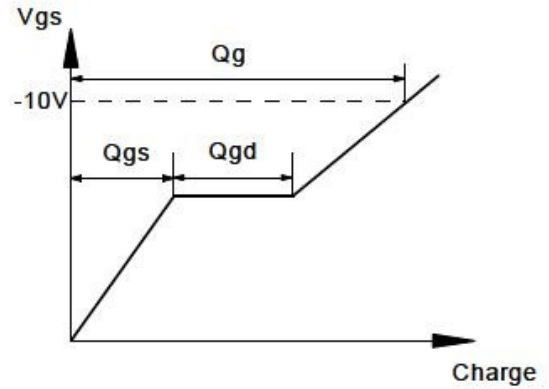
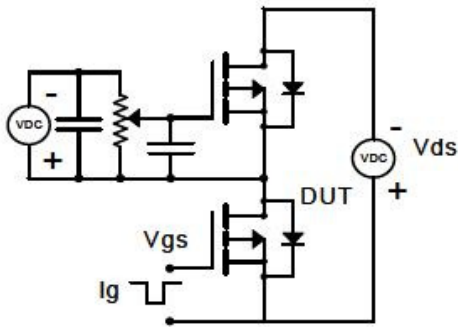
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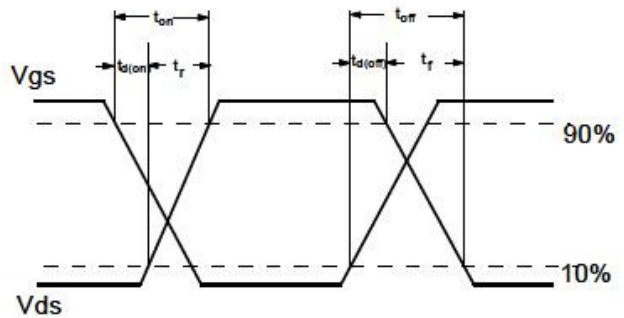
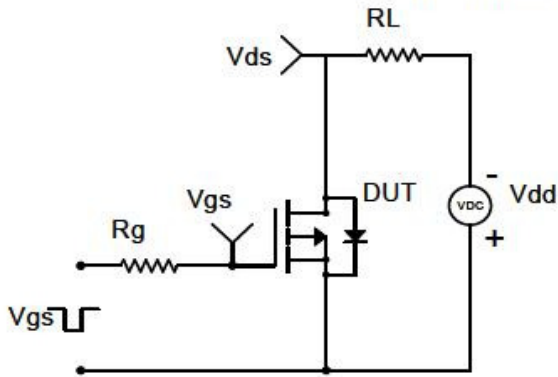


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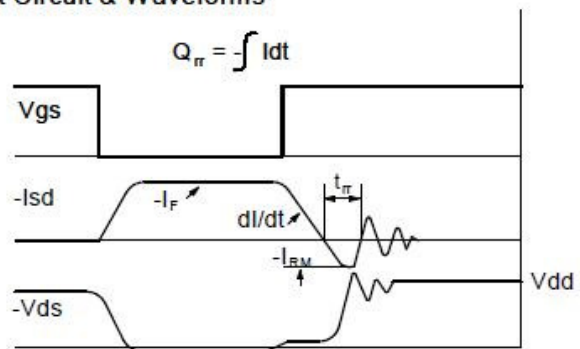
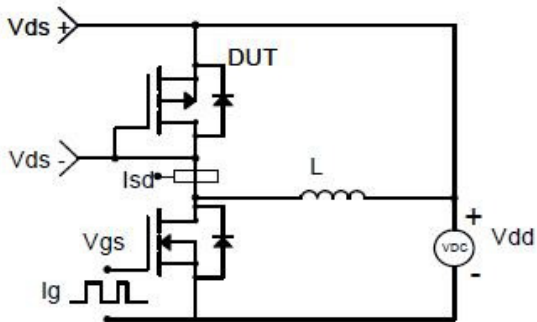
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

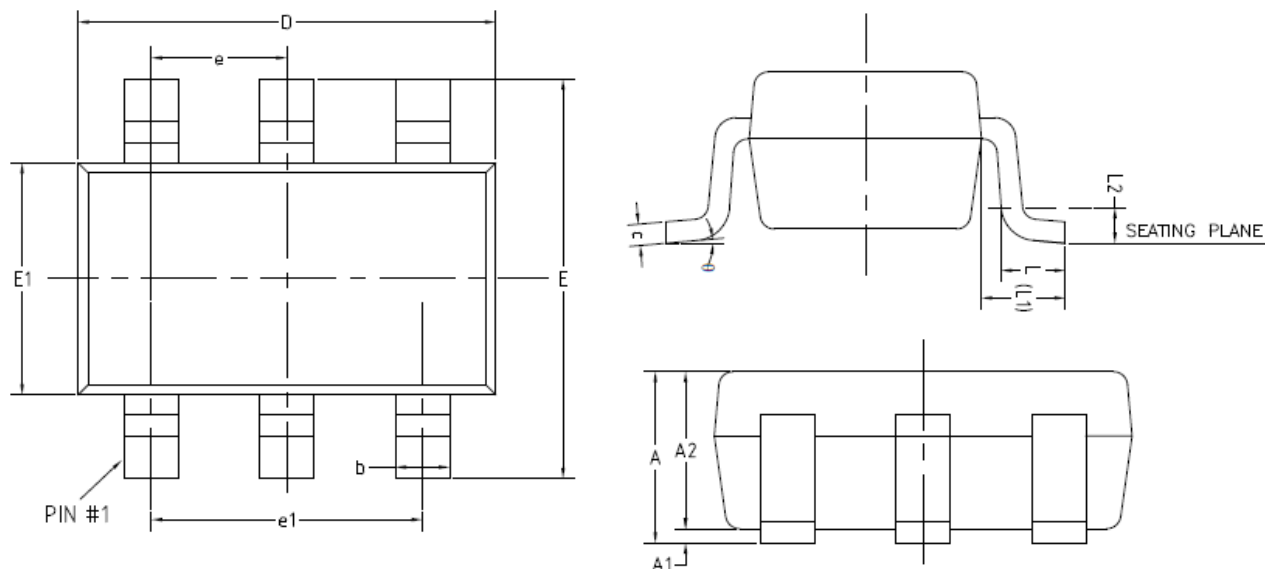


Diode Recovery Test Circuit & Waveforms





Package Information (TSOP-6)



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	0.70	—	0.90
A1	0	—	0.10
A2	0.70	0.75	0.80
b	0.35	—	0.50
c	0.08	—	0.20
D	2.82	2.92	3.02
E	2.65	2.80	2.95
E1	1.60	1.65	1.70
e	0.95(BSC)		
e1	1.90(BSC)		
L	0.30	0.45	0.60
L1	0.59REF		
L2	0.25BSC		
θ	0°	—	8°

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